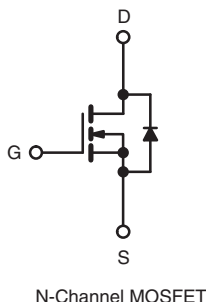
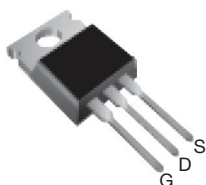


## Power MOSFET

### PRODUCT SUMMARY

|                           |                  |      |
|---------------------------|------------------|------|
| $V_{DS}$ (V)              | 100              |      |
| $R_{DS(on)}$ ( $\Omega$ ) | $V_{GS} = 5.0$ V | 0.27 |
| $Q_g$ (Max.) (nC)         | 12               |      |
| $Q_{gs}$ (nC)             | 3.0              |      |
| $Q_{gd}$ (nC)             | 7.1              |      |
| Configuration             | Single           |      |

**TO-220AB**


### FEATURES

- Dynamic  $dV/dt$  Rating
- Repetitive Avalanche Rated
- Logic-Level Gate Drive
- $R_{DS(on)}$  Specified at  $V_{GS} = 4$  V and 5 V
- 175 °C Operating Temperature
- Fast Switching
- Ease of Paralleling
- Compliant to RoHS Directive 2002/95/EC


**RoHS\***  
COMPLIANT

### DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220AB package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 W. The low thermal resistance and low package cost the TO-220AB contribute to its wide acceptance throughout the industry.

### ORDERING INFORMATION

|                |                         |
|----------------|-------------------------|
| Package        | TO-220AB                |
| Lead (Pb)-free | IRL520PbF<br>SiHL520-E3 |
| SnPb           | IRL520<br>SiHL520       |

### ABSOLUTE MAXIMUM RATINGS ( $T_C = 25$ °C, unless otherwise noted)

| PARAMETER                                        | SYMBOL           | LIMIT            | UNIT     |
|--------------------------------------------------|------------------|------------------|----------|
| Drain-Source Voltage                             | $V_{DS}$         | 100              | V        |
| Gate-Source Voltage                              | $V_{GS}$         | $\pm 10$         |          |
| Continuous Drain Current                         | $I_D$            | $T_C = 25$ °C    | A        |
|                                                  |                  | $T_C = 100$ °C   |          |
| Pulsed Drain Current <sup>a</sup>                | $I_{DM}$         | 36               |          |
| Linear Derating Factor                           |                  | 0.40             | W/°C     |
| Single Pulse Avalanche Energy <sup>b</sup>       | $E_{AS}$         | 170              | mJ       |
| Avalanche Current <sup>a</sup>                   | $I_{AR}$         | 9.2              | A        |
| Repetitive Avalanche Energy <sup>a</sup>         | $E_{AR}$         | 6.0              | mJ       |
| Maximum Power Dissipation                        | $P_D$            | 60               | W        |
| Peak Diode Recovery $dV/dt$ <sup>c</sup>         | $dV/dt$          | 5.5              | V/ns     |
| Operating Junction and Storage Temperature Range | $T_J, T_{stg}$   | - 55 to + 175    | °C       |
| Soldering Recommendations (Peak Temperature)     | for 10 s         | 300 <sup>d</sup> |          |
| Mounting Torque                                  | 6-32 or M3 screw | 10               | lbf · in |
|                                                  |                  | 1.1              | N · m    |

#### Notes

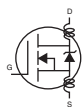
- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 25$  V, starting  $T_J = 25$  °C,  $L = 3.0$  mH,  $R_g = 25$   $\Omega$ ,  $I_{AS} = 9.2$  A (see fig. 12).
- $I_{SD} \leq 9.2$  A,  $dI/dt \leq 110$  A/ $\mu$ s,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 175$  °C.
- 1.6 mm from case.

\* Pb containing terminations are not RoHS compliant, exemptions may apply

**THERMAL RESISTANCE RATINGS**

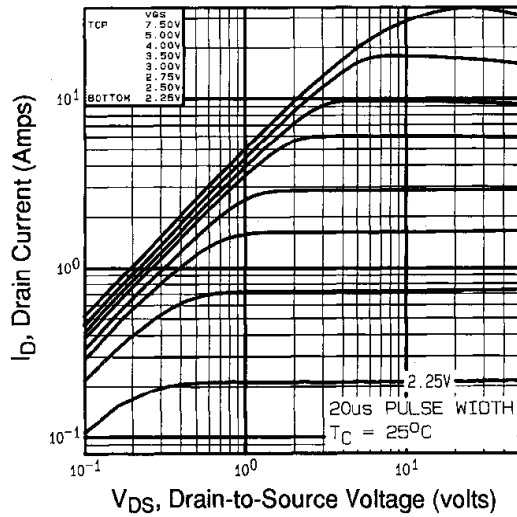
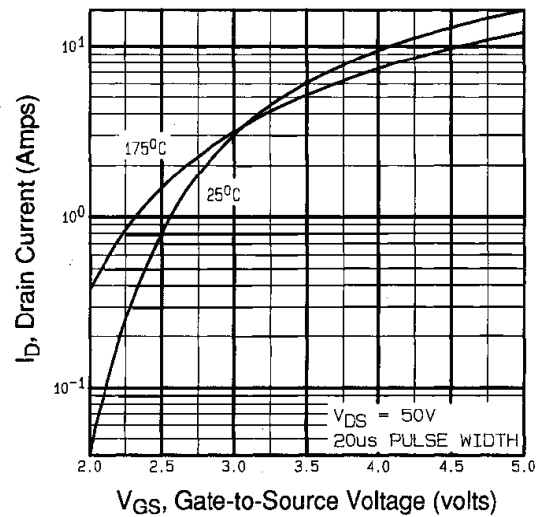
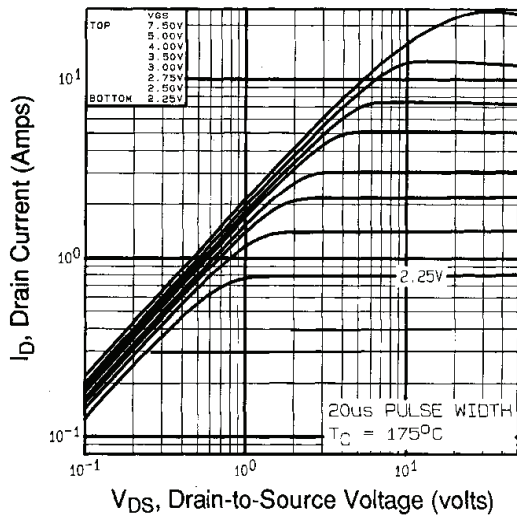
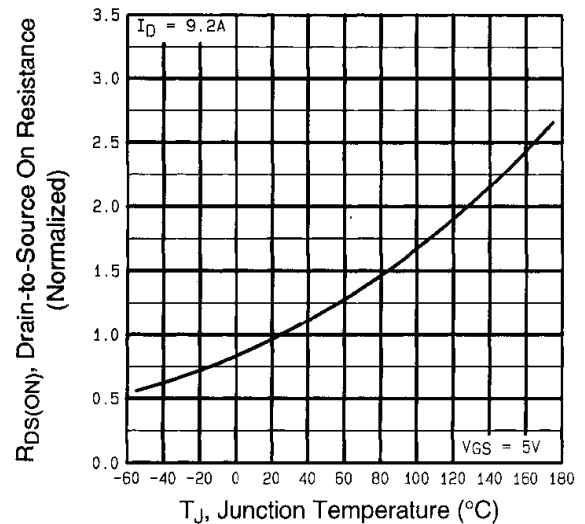
| PARAMETER                          | SYMBOL     | TYP. | MAX. | UNIT |
|------------------------------------|------------|------|------|------|
| Maximum Junction-to-Ambient        | $R_{thJA}$ | -    | 62   | °C/W |
| Case-to-Sink, Flat, Greasd Surface | $R_{thCS}$ | 0.50 | -    |      |
| Maximum Junction-to-Case (Drain)   | $R_{thJC}$ | -    | 2.5  |      |

**SPECIFICATIONS** ( $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

| PARAMETER                                 | SYMBOL                           | TEST CONDITIONS                                                                                                                                                 |                                                                                   | MIN. | TYP. | MAX.  | UNIT |
|-------------------------------------------|----------------------------------|-----------------------------------------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------|------|------|-------|------|
| Static                                    |                                  |                                                                                                                                                                 |                                                                                   |      |      |       |      |
| Drain-Source Breakdown Voltage            | V <sub>DS</sub>                  | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA                                                                                                                  |                                                                                   | 100  | -    | -     | V    |
| V <sub>DS</sub> Temperature Coefficient   | ΔV <sub>DS</sub> /T <sub>J</sub> | Reference to 25 °C, I <sub>D</sub> = 1 mA                                                                                                                       |                                                                                   | -    | 0.12 | -     | V/°C |
| Gate-Source Threshold Voltage             | V <sub>GS(th)</sub>              | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                                                                     |                                                                                   | 1.0  | -    | 2.0   | V    |
| Gate-Source Leakage                       | I <sub>GSS</sub>                 | V <sub>GS</sub> = ± 10 V                                                                                                                                        |                                                                                   | -    | -    | ± 100 | nA   |
| Zero Gate Voltage Drain Current           | I <sub>DSS</sub>                 | V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V                                                                                                                  |                                                                                   | -    | -    | 25    | μA   |
|                                           |                                  | V <sub>DS</sub> = 80 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C                                                                                          |                                                                                   | -    | -    | 250   |      |
| Drain-Source On-State Resistance          | R <sub>DS(on)</sub>              | V <sub>GS</sub> = 5.0 V                                                                                                                                         | I <sub>D</sub> = 5.5 A <sup>b</sup>                                               | -    | -    | 0.27  | Ω    |
|                                           |                                  | V <sub>GS</sub> = 4.0 V                                                                                                                                         | I <sub>D</sub> = 4.6 A <sup>b</sup>                                               | -    | -    | 0.38  |      |
| Forward Transconductance                  | g <sub>fs</sub>                  | V <sub>DS</sub> = 50 V, I <sub>D</sub> = 5.5 A                                                                                                                  |                                                                                   | 3.2  | -    | -     | S    |
| Dynamic                                   |                                  |                                                                                                                                                                 |                                                                                   |      |      |       |      |
| Input Capacitance                         | C <sub>iss</sub>                 | V <sub>GS</sub> = 0 V,<br>V <sub>DS</sub> = 25 V,<br>f = 1.0 MHz, see fig. 5                                                                                    |                                                                                   | -    | 490  | -     | pF   |
| Output Capacitance                        | C <sub>oss</sub>                 |                                                                                                                                                                 |                                                                                   | -    | 150  | -     |      |
| Reverse Transfer Capacitance              | C <sub>rss</sub>                 |                                                                                                                                                                 |                                                                                   | -    | 30   | -     |      |
| Total Gate Charge                         | Q <sub>g</sub>                   | V <sub>GS</sub> = 5.0 V                                                                                                                                         | I <sub>D</sub> = 9.2 A, V <sub>DS</sub> = 80 V,<br>see fig. 6 and 13 <sup>b</sup> | -    | -    | 12    | nC   |
| Gate-Source Charge                        | Q <sub>gs</sub>                  |                                                                                                                                                                 |                                                                                   | -    | -    | 3.0   |      |
| Gate-Drain Charge                         | Q <sub>gd</sub>                  |                                                                                                                                                                 |                                                                                   | -    | -    | 7.1   |      |
| Turn-On Delay Time                        | t <sub>d(on)</sub>               | V <sub>DD</sub> = 50 V, I <sub>D</sub> = 9.2 A,<br>R <sub>g</sub> = 9.0 Ω, R <sub>D</sub> = 5.2 Ω, see fig. 10 <sup>b</sup>                                     |                                                                                   | -    | 9.8  | -     | ns   |
| Rise Time                                 | t <sub>r</sub>                   |                                                                                                                                                                 |                                                                                   | -    | 64   | -     |      |
| Turn-Off Delay Time                       | t <sub>d(off)</sub>              |                                                                                                                                                                 |                                                                                   | -    | 21   | -     |      |
| Fall Time                                 | t <sub>f</sub>                   |                                                                                                                                                                 |                                                                                   | -    | 27   | -     |      |
| Internal Drain Inductance                 | L <sub>D</sub>                   | Between lead,<br>6 mm (0.25") from<br>package and center of<br>die contact  |                                                                                   | -    | 4.5  | -     | nH   |
| Internal Source Inductance                | L <sub>S</sub>                   |                                                                                                                                                                 |                                                                                   | -    | 7.5  | -     |      |
| Drain-Source Body Diode Characteristics   |                                  |                                                                                                                                                                 |                                                                                   |      |      |       |      |
| Continuous Source-Drain Diode Current     | I <sub>S</sub>                   | MOSFET symbol<br>showing the<br>integral reverse<br>p - n junction diode    |                                                                                   | -    | -    | 9.2   | A    |
| Pulsed Diode Forward Current <sup>a</sup> | I <sub>SM</sub>                  |                                                                                                                                                                 |                                                                                   | -    | -    | 36    |      |
| Body Diode Voltage                        | V <sub>SD</sub>                  | T <sub>J</sub> = 25 °C, I <sub>S</sub> = 9.2 A, V <sub>GS</sub> = 0 V <sup>b</sup>                                                                              |                                                                                   | -    | -    | 2.5   | V    |
| Body Diode Reverse Recovery Time          | t <sub>rr</sub>                  | T <sub>J</sub> = 25 °C, I <sub>F</sub> = 9.2 A, dI/dt = 100 A/μs <sup>b</sup>                                                                                   |                                                                                   | -    | 130  | 190   | ns   |
| Body Diode Reverse Recovery Charge        | Q <sub>rr</sub>                  |                                                                                                                                                                 |                                                                                   | -    | 0.83 | 1.0   | μC   |
| Forward Turn-On Time                      | t <sub>on</sub>                  | Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub> )                                                               |                                                                                   |      |      |       |      |

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).  
b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Fig. 1 - Typical Output Characteristics,  $T_C = 25^\circ\text{C}$** 

**Fig. 3 - Typical Transfer Characteristics**

**Fig. 2 - Typical Output Characteristics,  $T_C = 175^\circ\text{C}$** 

**Fig. 4 - Normalized On-Resistance vs. Temperature**

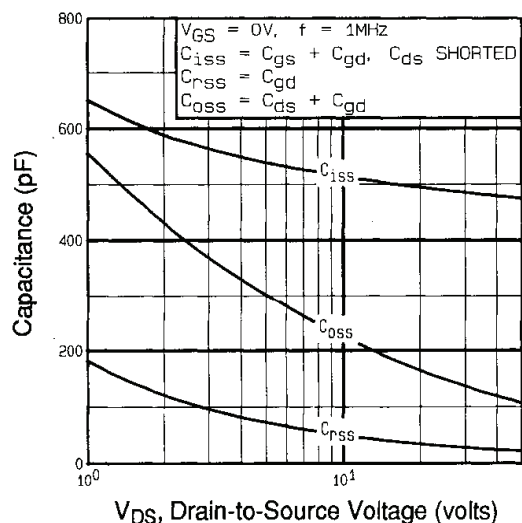


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

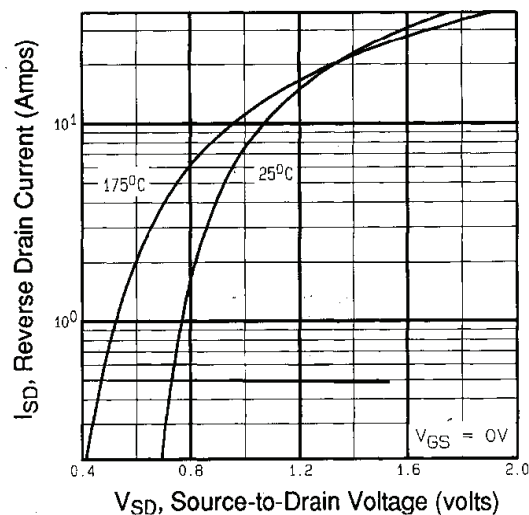


Fig. 7 - Typical Source-Drain Diode Forward Voltage

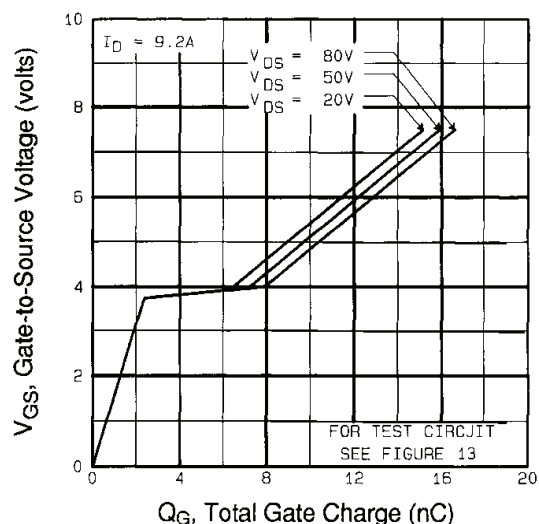


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

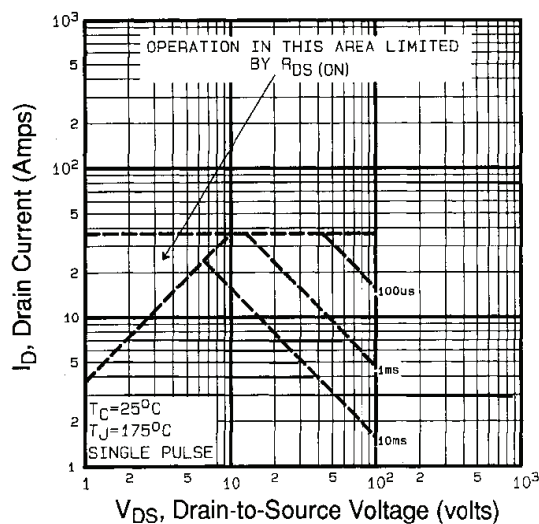
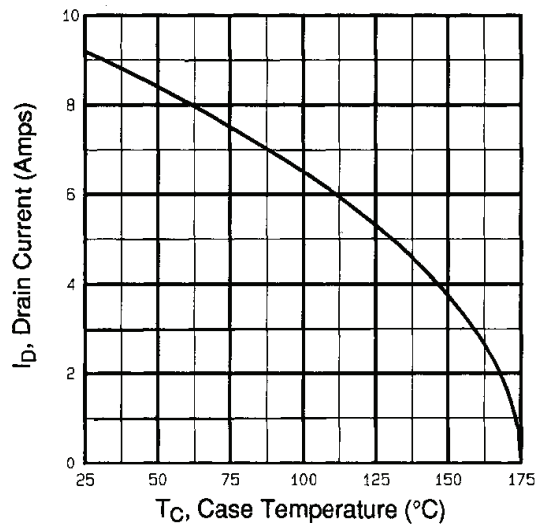
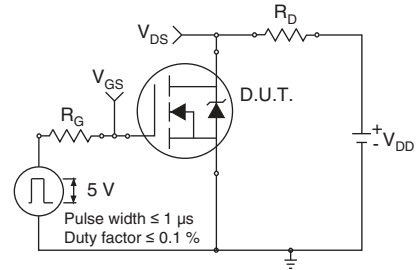
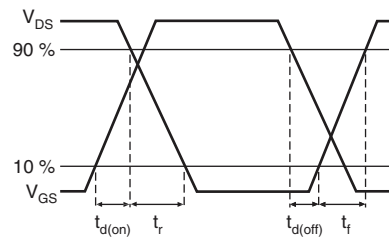
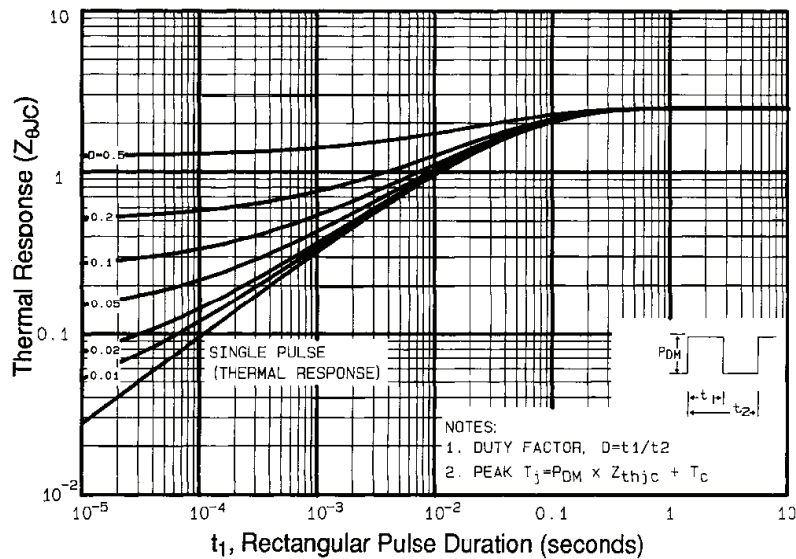


Fig. 8 - Maximum Safe Operating Area


**Fig. 9 - Maximum Safe Operating Area**

**Fig. 10a - Switching Time Test Circuit**

**Fig. 10b - Switching Time Waveforms**

**Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case**

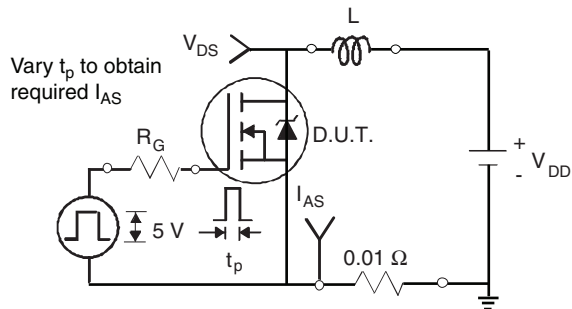


Fig. 12a - Unclamped Inductive Test Circuit

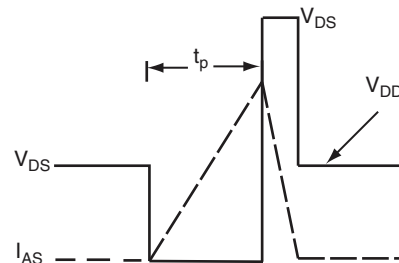


Fig. 12b - Unclamped Inductive Waveforms

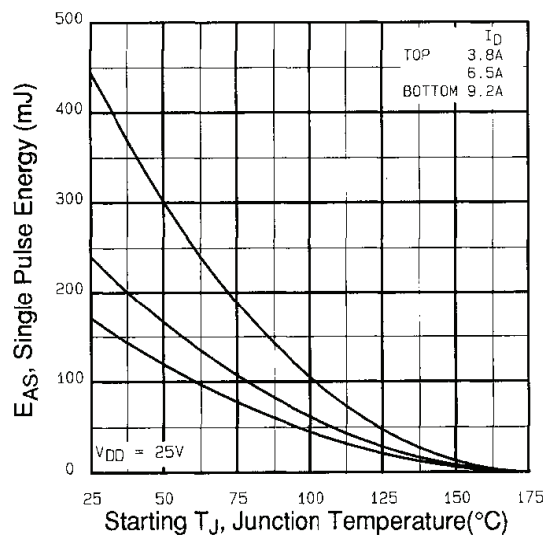


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

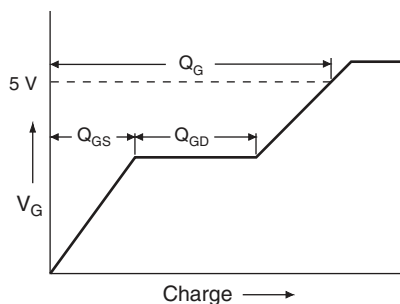


Fig. 13a - Basic Gate Charge Waveform

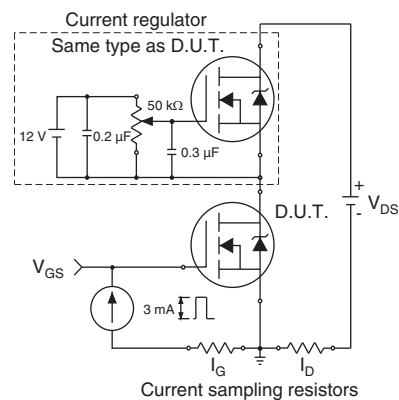


Fig. 13b - Gate Charge Test Circuit


**Fig. 14 - For N-Channel**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?91298](http://www.vishay.com/ppg?91298).

## TO-220AB



| DIM.            | MILLIMETERS |       | INCHES |       |
|-----------------|-------------|-------|--------|-------|
|                 | MIN.        | MAX.  | MIN.   | MAX.  |
| A               | 4.25        | 4.65  | 0.167  | 0.183 |
| b               | 0.69        | 1.01  | 0.027  | 0.040 |
| b(1)            | 1.20        | 1.73  | 0.047  | 0.068 |
| c               | 0.36        | 0.61  | 0.014  | 0.024 |
| D               | 14.85       | 15.49 | 0.585  | 0.610 |
| E               | 10.04       | 10.51 | 0.395  | 0.414 |
| e               | 2.41        | 2.67  | 0.095  | 0.105 |
| e(1)            | 4.88        | 5.28  | 0.192  | 0.208 |
| F               | 1.14        | 1.40  | 0.045  | 0.055 |
| H(1)            | 6.09        | 6.48  | 0.240  | 0.255 |
| J(1)            | 2.41        | 2.92  | 0.095  | 0.115 |
| L               | 13.35       | 14.02 | 0.526  | 0.552 |
| L(1)            | 3.32        | 3.82  | 0.131  | 0.150 |
| $\varnothing P$ | 3.54        | 3.94  | 0.139  | 0.155 |
| Q               | 2.60        | 3.00  | 0.102  | 0.118 |

ECN: X12-0208-Rev. N, 08-Oct-12  
DWG: 5471

### Notes

- \*  $M = 1.32$  mm to  $1.62$  mm (dimension including protrusion)  
Heatsink hole for HVM
- Xi'an and Mingxin actual photo





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**Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.**

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Электрон  
Связь**

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